

BUK763R9-60E

N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|--|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 60 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | - | 100 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 263 | W |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11 | | - | 2.94 | 3.9 | mΩ |
| Dynamic characteristics | | | | | | | |
| Q_{GD} | gate-drain charge | I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13; Fig. 14 | | - | 33 | - | nC |

^[1] Continuous current is limited by package.



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | G | gate | mb | D I |
| 2 | D | drain | | |
| 3 | S | source | | G |
| mb | D | mounting base; connected to drain | 1 3 | mbb076 S |
| | | | D2PAK (SOT404) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| BUK763R9-60E | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| BUK763R9-60E | BUK763R9-60E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 60 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω | | - | 60 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | 263 | W |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> | [1] | - | 100 | Α |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u> | [1] | - | 100 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3 | | - | 706 | Α |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| T _j | junction temperature | | | -55 | 175 | °C |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|--------|-----|-----|------|
| Source-dra | nin diode | | | | | |
| Is | source current | T _{mb} = 25 °C | [1] | - | 100 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 706 | Α |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 100 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; V_{GS} = 60 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [2][3] | - | 372 | mJ |

- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

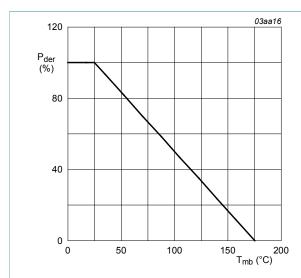
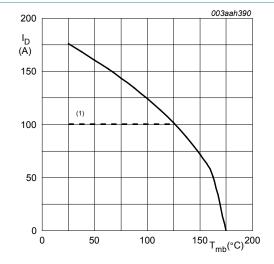


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

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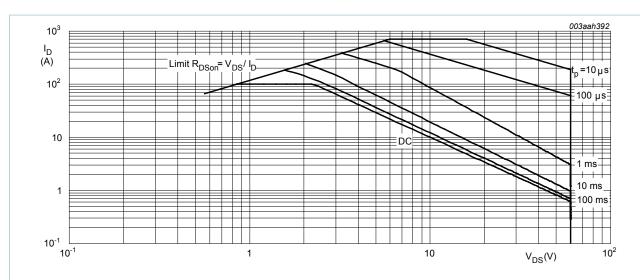
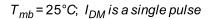


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



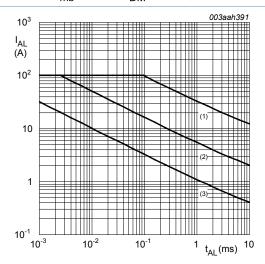


Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

9. Thermal characteristics

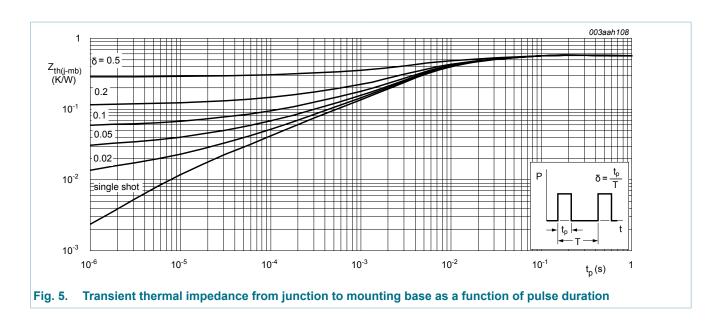
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | - | 0.57 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed-circuit board | - | 50 | - | K/W |

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---|----------------------------------|---|-----|------|-----|------|
| Static chara | acteristics | | | | | , |
| V _{(BR)DSS} drain-source breakdown voltage | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 60 | - | - | V |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 54 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| I _{DSS} drain leak | drain leakage current | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.07 | 1 | μA |
| | | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 2.94 | 3.9 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | - | 8.5 | mΩ |
| Dynamic ch | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; | - | 103 | - | nC |
| Q _{GS} | gate-source charge | Fig. 13; Fig. 14 | - | 25.1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 33 | - | nC |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|-----|------|------|------|
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$ | - | 5609 | 7480 | pF |
| C _{oss} | output capacitance | | - | 737 | 884 | pF |
| C _{rss} | reverse transfer capacitance | | - | 455 | 624 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 45 V; R_{L} = 1.8 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω | - | 25.3 | - | ns |
| t _r | rise time | | - | 41.4 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 62.7 | - | ns |
| t _f | fall time | | - | 45 | - | ns |
| L _D | internal drain inductance | from upper edge of mounting base to centre of die | - | 2.5 | - | nH |
| L _S | internal source inductance | measured from source lead to source bond pad | - | 7.5 | - | nH |
| Source-dra | in diode | - | | | | |
| V _{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 39 | - | ns |
| Q _r | recovered charge | V _{DS} = 25 V | - | 51 | - | nC |

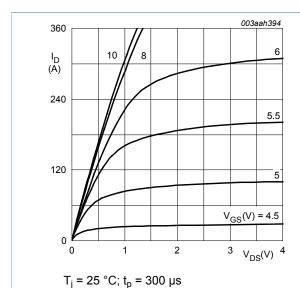


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

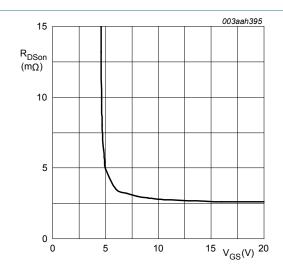


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 25A$

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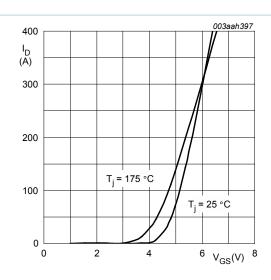


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



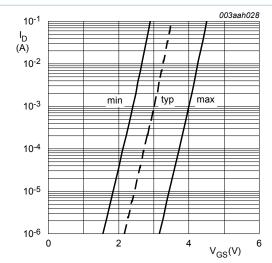


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

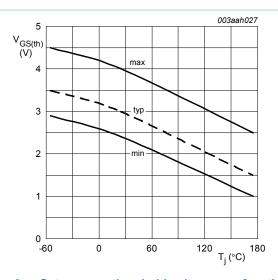


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}

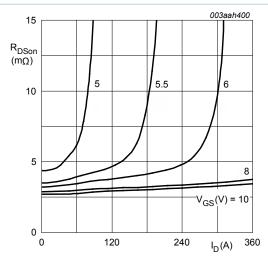


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

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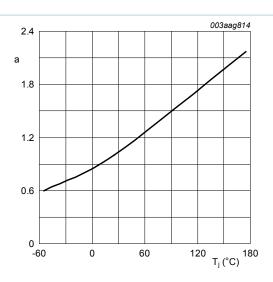


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25 \, ^{\circ}\text{C})}}$$

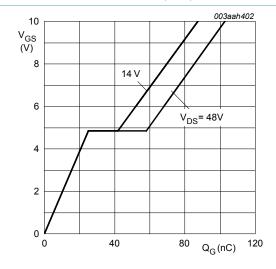


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

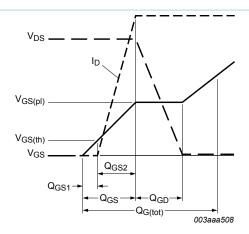


Fig. 13. Gate charge waveform definitions

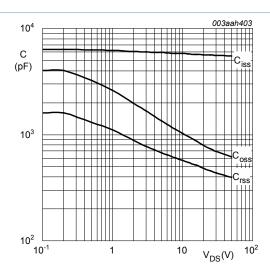


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

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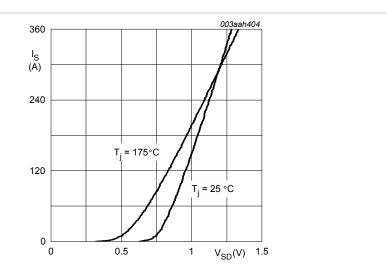
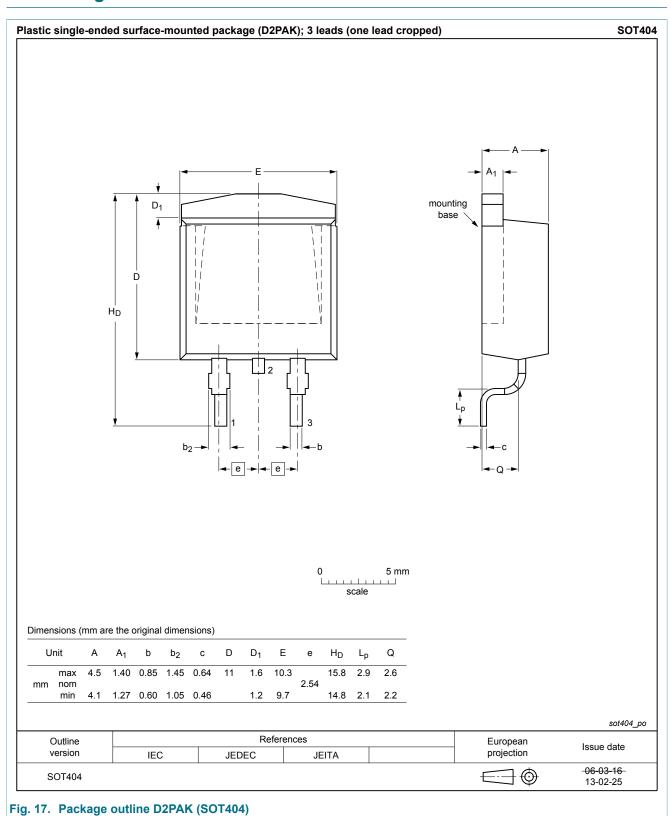


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

11. Package outline



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12. Legal information

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|--------------------------------------|--------------------|---|
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